## Fabrication of single-crystal diamond nano-slabs for photonic applications

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Production of photonic nanostructures in diamond membranes for interactions between embedded color centers, such as negatively charged nitrogen vacancy (NV<sup>-</sup>) centers, with confined optical modes are nearly within reach of current fabrication techniques. Demonstration of such regimes in light-matter interactions would secure diamond as a viable platform for quantum information processing<sup>1</sup>. The advent of optically thin membranes in other semiconductor materials has enabled the development of a variety of nano-photonic devices. However, a remaining challenge concerns the growth of high-quality, singlecrystal diamond membranes on lattice-matched substrates.

Here, we introduce an approach to fabricate thin, tall slabs of diamond by vertically etching a single-crystal diamond plate that is commercially available (Fig. 1). These diamond nano-slabs can then be mechanically removed from the bulk diamond plate for further processing, so that the plate may be reused after polishing for nano-slab fabrication. To produce slabs that are nearly vertical and deep enough to accommodate micro- and nano-photonic devices, we have developed a new process that alternates between plasma etching and mask deposition steps, similar to the Bosch process used in deep reactive ion etching. This process enables vertical nano-slabs with aspect ratios (height: thickness) of about 50, including 200-nm-thick slabs that are 10 µm tall (Fig. 2). We mechanically separate the nano-slabs from the parent bulk diamond, and implant NV<sup>-</sup> centers (Fig. 3a). Spin-echo experiments<sup>2</sup> indicate that the NV<sup>-</sup> centers in the nano-slabs exhibit very long spin coherence times that approach 100 µs, which is comparable to high-quality bulk diamond. When necessary, we thin the nanoslabs using plasma etching to the desired thickness. These above-mentioned dimensions are suitable for a range of nano-photonic devices. In particular, we pattern two-dimensional photonic crystal cavities into them using focused ion beam (FIB)<sup>3</sup>. We also confirm that the material properties of nano-slabs produced using only plasmas etching processing are indistinguishable from the parent bulk diamond using Raman scattering characteristic (Fig. 3b).

<sup>&</sup>lt;sup>1</sup> A. Igor, A. Greentree, and S. Prawer, Nature Photonics, 5(7), pp.397-405 (2011).

<sup>&</sup>lt;sup>2</sup> J. Hodges, L. Li, M. Lu, E. Chen, M. Trusheim, S. Allegri, X. Yao, O. Gaathon, H. Bakhru, and D. Englund. New Journal of Physics, 14(9):093004, 2012.

<sup>&</sup>lt;sup>3</sup> J. Riedrich-Moller et al, Nat Nanotechnology, 7(1):69-74, Jan 2012.



*Figure 1: Fabrication procedure.* (a) e-beam resist coating; (b) e-beam lithography and development; (c) initial oxygen plasma etching of diamond; (d) and (e) Cr deposition at an oblique angle; (f) continued oxygen plasma etching of diamond; (g) mechanically separated diamond nano-slabs from diamond; (h) diamond nano-slabs transferred to a patterned silicon substrate; (i) further thinning of diamond nano-slabs with oxygen or chlorine plasma etching.



Figure 2: Scanning electron microscope images of diamond nano-slabs (a) before and (b) after mechanical separation. The inset image shows one diamond nano-slab transferred onto patterned silicon substrate and thinned with plasma etching to  $\sim 200$  nm.



*Figure 3*: (a) Spectrum of fluorescence from one NV<sup>-</sup> center in the fabricated nanoslabs clearly showing the presence of the zero-phonon-line (ZPL) at 637nm. b) Raman scattering spectra from parent diamond, FIB damaged diamond and fabricated diamond nano-slabs showing the quality of nano-slabs is distinguishable from parent diamond.